

Docket No. 219723US2S

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Hajime NAGANO, et al.

SERIAL NO: NEW APPLICATION

GAU:

FILED: HEREWITH

EXAMINER:

FOR: SEMICONDUCTOR DEVICE USING PARTIAL SOI SUBSTRATE AND MANUFACTURING METHOD THEREOF

#2/5902  
1c872 U.S. PTO  
10/078344  
02/21/02

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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**STATEMENT OF RELEVANCY**

**Reference AO (2000-243944) on form PTO-1449:**

This patent describes about the process and structure of partial SOI water. The point of this process is that selective epitaxial growth was started from only the surface of SOI base water and CMP process is used to get flat surface of partial SOI water.

**Reference AP (11-17001) on form PTO-1449:**

This patent describes about the process and structure of partial SOI water. Double spacer, which are made of insulator and conductor, rounds the bulk area and the conductor is touched with SOI-layer. This structure enables to suppress and the conductor is touched with SOI-layer. This structure enables to suppress the body floating effect and to separate SOI area from bulk area electrically.

**Reference AQ (8-17694) on form PTO-1449:**

This patent describes about the proses and structure of partial SOI water. SIMOX process and Si epitaxial growth process are presented. The point of this process is that CMP process is used to get flat surface of partial SOI water.